

**Notice of References Cited**

Application/Control No.

10/797,231

Applicant(s)/Patent Under  
Reexamination  
HAMMOND ET AL.

Examiner

Alexander G. Ghyka

Art Unit

2812

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ismail, Si/SiGe High Speed Field Effect Transistors, IEEE 1995.
	V	Chang et al, Selective Etching of SiGe on SiGe/Si Heterostructures, J. Electrochem, Soc. Vol. 138, No.1, 1991
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

*Alex Ghyka* 11/12/06